L	Hits	Search Text	DB	Time stamp
Number				
1	44	438/197,230,231,289,290,298,301,302,303,30		2004/05/25
		and (field adj effect adj transistor) and	US-PGPUB;	15:49
		(ion adj implant) and (angl\$3 with dopant)	EPO; JPO; DERWENT	
2	19	(field adj effect adj transistor) and	USPAT;	2004/05/25
2	10	(ion adj implant) and (angl\$3 with	US-PGPUB;	15:46
		dopant) and (gate adj electrode) and	EPO; JPO;	
:		(source) and (drain) and (mask with	DERWENT	
		spacer)	IICDAM.	2004/05/25
3	11	438/525.ccls. and (field adj effect adj transistor) and (ion adj implant) and	USPAT; US-PGPUB;	15:46
		(angl\$3 with dopant)	EPO; JPO;	15.10
		(angrio mran departe)	DERWENT	
4	112	(field adj effect adj transistor) and	USPAT;	2004/05/25
		(ion adj implant) and (angl\$3 with	US-PGPUB;	15:47
		dopant)	EPO; JPO; DERWENT	
5	73	(field adj effect adj transistor) and	USPAT;	2004/05/25
J	, ,	(ion adj implant) and (angl\$3 with	US-PGPUB;	15:48
		dopant) and @ad<20010716	EPO; JPO;	
			DERWENT	2004/05/25
6	33	438/197,230,231,289,290,298,301,302,303,30 and (field adj effect adj transistor) and	5µS ēAT \$. US-PGPUB;	2004/05/25 15:50
		(ion adj implant) and (angl\$3 with	EPO; JPO;	15.50
		dopant) and @ad<20010716	DERWENT	
7	o	438/197,230,231,289,290,298,301,302,303,30	5USEATs.	2004/05/25
1		and (field adj effect adj transistor) and	US-PGPUB;	15:51
		(ion adj implant) and (angl\$3 with	EPO; JPO;	' I
	7	dopant) and @ad<20010716 and (inplant\$7	DERWENT	2004/05/25
8	'	and (field adj effect adj transistor) and	US-PGPUB;	15:51
		(ion adj implant) and (angl\$3 with	EPO; JPO;	
		dopant) and @ad<20010716 and (implant\$7	DERWENT	
9	33	43m/107n/di0t031,289,290,298,301,302,303,30	5USPATs.	2004/05/25
		and (field adj effect adj transistor) and	US-PGPUB; EPO; JPO;	15:52
	1	(ion adj implant) and (angl\$3 with dopant) and @ad<20010716 and (implant\$7	DERWENT	
10	33	4881\$67c0B64286r\$89,290,298,301,302,303,30		2004/05/25
"		and (field adj effect adj transistor) and	US-PGPUB;	15:54
		(ion adj implant) and (angl\$3 with	EPO; JPO;	
		dopant) and @ad<20010716 and (implant\$7	DERWENT USPAT;	2003/11/03
_	2124	néasta edndaffert adj transistor) and (ion adj implant)	US-PGPUB;	16:16
		(1011 ad) Implant)	EPO; JPO;	
			DERWENT	
-	6		USPAT;	2004/05/25 15:46
		transistor) and (ion adj implant) and	US-PGPUB; EPO; JPO;	15:46
1		(angl\$3 with dopant)	DERWENT	
_	85	(field adj effect adj transistor) and	USPAT;	2004/05/25
		(ion adj implant) and (angl\$3 with	US-PGPUB;	15:47
		dopant)	EPO; JPO;	
	34	(field adj effect adj transistor) and	DERWENT USPAT;	2003/06/20
-	34	(ion adj implant) and (angl\$3 with	US-PGPUB;	18:56
		dopant) and (gate adj electrode)	EPO; JPO;	
			DERWENT	2002/06/03
-	. 34	(field adj effect adj transistor) and	USPAT;	2003/06/21
1		(ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and	US-PGPUB; EPO; JPO;	13.77
1		(source) and (drain)	DERWENT	
_	5	(field adj effect adj transistor) and	USPAT;	2003/06/20
1		(ion adj implant) and (angl\$3 with	US-PGPUB;	18:59
		dopant) and (gate adj electrode) and	EPO; JPO;	
		(source) and (drain) and (lithography) (field adj effect adj transistor) and	DERWENT USPAT;	2003/10/30
_	1	(ion adj implant) and (angl\$3 with	US-PGPUB;	08:59
		dopant) and (gate adj electrode) and	EPO; JPO;	
		(source) and (drain) and (pocket adj	DERWENT	
	1	region)	<u></u>	<u> </u>

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	.1:				
-		4	438/197.ccls. and (field adj effect adj	USPAT;	2004/05/25
			transistor) and (ion adj implant) and	US-PGPUB;	15:44
			(angl\$3 with dopant)	EPO; JPO;	
				DERWENT	
-		27	(field adj effect adj transistor) and	USPAT;	2003/06/20
	İ		(ion adj implant) and (angl\$3 with	US-PGPUB;	19:04
'	ŀ		dopant) and (gate adj electrode) and	EPO; JPO;	
1			(source) and (drain) and (mask)	DERWENT	
-		0	(field adj effect adj transistor) and	USPAT;	2003/06/20
ì			(ion adj implant) and (angl\$3 with	US-PGPUB;	19:05
1	ł		dopant) and (gate adj electrode) and	EPO; JPO;	
			(source) and (drain) and (mask) and	DERWENT	
		i	(conductive adj region)		i
_		5	(field adj effect adj transistor) and	USPAT;	2003/06/20
			(ion adj implant) and (angl\$3 with	US-PGPUB;	19:05
			dopant) and (gate adj electrode) and	EPO; JPO;	
	1		(source) and (drain) and (mask) and	DERWENT	
			(conductive adj layer)		
l _		6	(field adj effect adj transistor) and	USPAT;	2003/06/20
		-	(ion adj implant) and (angl\$3 with	US-PGPUB;	19:06
			dopant) and (gate adj electrode) and	EPO; JPO;	
			(source) and (drain) and (mask) and	DERWENT	
1			(conduct\$3 adj layer)		
1_		18	(field adj effect adj transistor) and	USPAT;	2004/05/25
1	j	10	(ion adj implant) and (angl\$3 with	US-PGPUB;	15:46
			dopant) and (gate adj electrode) and	EPO; JPO;	
		1	(source) and (drain) and (mask with	DERWENT	
			electrode)		
	l	12	(field adj effect adj transistor) and	USPAT;	2004/05/25
-		12	(ion adj implant) and (angl\$3 with	US-PGPUB;	15:46
			dopant) and (gate adj electrode) and	EPO; JPO;	
	İ	i	(source) and (drain) and (mask with	DERWENT	
•	i		spacer)		
Ì		1	(field adj effect adj transistor) and	USPAT;	2003/06/21
-	ł	1	(ion adj implant) and (angl\$3 with	US-PGPUB;	15:57
1			dopant) and (gate adj electrode) and	EPO; JPO;	
1			(source) and (drain) and (mask with	DERWENT	i i
			dielectric adj spacer)		
		o	(field adj effect adj transistor) and	USPAT;	2003/06/21
-		١	(ion adj implant) and (angl\$3 with	US-PGPUB;	16:07
			dopant) and (gate adj electrode) and	EPO; JPO;	
		i	(source) and (drain) and (taper with	DERWENT	
	1		electrode)		
		0	(field adj effect adj transistor) and	USPAT;	2003/06/21
-		U	(ion adj implant) and (angl\$3 with	US-PGPUB;	16:11
			dopant) and (gate adj electrode) and	EPO; JPO;	
1]		(source) and (drain) and (taper\$2 with	DERWENT	
			electrode)	1	
1_		5	(field adj effect adj transistor) and	USPAT;	2003/06/21
-			(ion adj implant) and (angl\$3 with	US-PGPUB;	16:12
			dopant) and (gate adj electrode) and	EPO; JPO;	
			(source) and (drain) and (reduced with	DERWENT	
			electrode)		į į
1_			EP-1263027\$.did.	USPAT;	2003/06/27
-				US-PGPUB;	08:41
				EPO; JPO;	[
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_		2	EP-1263027-\$.did.	USPAT;	2003/06/27
1-		2	1200027 4.414.	US-PGPUB;	09:04
1				EPO; JPO;	
1				DERWENT	1
1_		12213048	US 5731239.pn.	USPAT;	2003/06/27
l -		12213040	00 0701005.p.i.	US-PGPUB;	08:54
		}		EPO; JPO;	
1		1		DERWENT	
_		2	5731239.pn.	USPAT;	2003/06/27
-			,	US-PGPUB;	08:57
				EPO; JPO;	ļ l
				DERWENT	
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۲=		4	512063.pn.	US-PGPUB;	08:58
				EPO; JPO;	00.00
i					
				DERWENT	2003/06/27
l –		2	5120637.pn.	USPAT;	08:58
	ŀ			US-PGPUB;	08:38
ì				EPO; JPO;	
				DERWENT	
_		2	5120673.pn.	USPAT;	2003/06/27
-	i			US-PGPUB;	09:10
	į			EPO; JPO;	
1				DERWENT	
İ		ا ه	JP-88317951-\$.did.	USPAT;	2003/06/27 .
-		١	0F-00317331 4.414.	US-PGPUB;	09:23
				EPO; JPO;	
ì				DERWENT	
		0	JP-2162738-\$.did.	USPAT;	2003/06/27
-		0	JP-2162736-9.drd.	US-PGPUB;	09:06
				EPO; JPO;	
				DERWENT	
1			A4 COTTOO TO A AND A	USPAT;	2003/06/27
-		0	JP-2162738 A-\$.did.	US-PGPUB;	09:07
1				EPO; JPO;	
				DERWENT	1
1				USPAT;	2003/06/27
-		2	5021355.pn.	i .	09:13
1				US-PGPUB;	05.13
1				EPO; JPO;	1
1				DERWENT	2003/06/27
_		2	6501133.pn.	USPAT;	
			-	US-PGPUB;	09:15
ı				EPO; JPO;	
1		•		DERWENT	1 (0.5 (0.7
i _		0	2020050621.pn.	USPAT;	2003/06/27
-			202000	US-PGPUB;	09:25
1				EPO; JPO;	
				DERWENT	
i		0	2000648044.pn.	USPAT;	2003/06/27
-		1	2000040044.pm.	US-PGPUB;	09:17
1				EPO; JPO;	
1		1		DERWENT	
			20020050621.pn.	USPAT;	2003/06/27
-	•	2	20020030621.pm.	US-PGPUB;	09:18
				EPO; JPO;	1
				DERWENT	
				USPAT;	2003/06/27
-	•	2	5731239.pn.	US-PGPUB;	09:19
1		1		EPO; JPO;	
-				DERWENT] 1
				USPAT;	2003/06/27
-	-	2	5120673.pn.	US-PGPUB;	09:19
			1	EPO; JPO;	~~ ~
				DERWENT	1
				I	2003/06/27
-	-	1	JP-56048174-\$.did.	USPAT; US-PGPUB;	09:23
1					05.25
-				EPO; JPO;	
1		1		DERWENT	2003/06/27
-	_	2	5021355.pn.	USPAT;	
		Ì		US-PGPUB;	09:25
		1		EPO; JPO;	
				DERWENT	1 0000 406 407
- .	_	10	438/525,197.ccls. and (field adj effect	USPAT;	2003/06/27
		1	adj transistor) and (ion adj implant) and	US-PGPUB;	10:11
1			(angl\$3 with dopant)	EPO; JPO;	1
			1	DERWENT	
1	_	221	mask with (dielectric adj spacer)	USPAT;	2003/10/30
		221	magn. with the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the control of the contro	US-PGPUB;	09:02
- 1				EPO; JPO;	1
-		ļ		DERWENT	
		14000	(advanced adj micro adj devices).asn.	USPAT;	2003/11/03
- 1		14806	(advanced adj micro adj dovices, same	US-PGPUB;	16:19
		1		EPO; JPO;	
				DERWENT	

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- 10 (advanced adj micro adj devices).asn. and USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT;	
- 10 (advanced adj micro adj devices).asn. and mask and shadow and gate adj electrode - 2003/11/03 16:20 - 38/519.ccls. and (advanced adj micro adj devices).asn. and mask and shadow and gate adj electrode - 10 (advanced adj micro adj devices).asn. and mask and shadow and gate adj electrode - 2003/11/03 16:20 2003/11/03 16:21 - 2003/11/03 16:21 - 2003/11/03 16:21 - 2003/11/03 16:21 - 2003/11/03 16:21 - 2003/11/03 16:26	
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and (mask same (reduced adj width)) and US-PGPUB; 16:28	
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0 (advanced adj micro adj devices).asn. USPAT; 2003/11/04	1
and (mask same reduced same width) and US-PGPOB, US-14	
shadow and gate adj electrode EPO; JPO; DERWENT	į
1 1	<u>.</u>
2 (advanced adj micro adj devices).asn. USPAT; 2003/11/04 and (mask same width) and shadow and gate US-PGPUB; 09:50	}
and (mask same width) and shadow and get EPO; JPO; adj electrode	
DERWENT	
2 (advanced adj micro adj devices).asn. USPAT; 2003/11/04	±
and (mask same width) and shadow and gate US-PGFOB,	
adj electrode and mask EPO; JPO; DERWENT	
USPAT; 2003/11/0	4
- 2 4198250.pn. US-PGPUB; 09:55	ŀ
EPO; JPO;	
DERWENT USPAT; 2003/11/0	<u> </u>
6 (advanced ad) micro adj devices/.asii.	1
and mask and shadow and gate adj	1
electrode and width EPO; JPO; DERWENT	1
212 (advanced adj micro adj devices).asn. USPAT; 2003/11/0	4
and mask and (gate same width same mask) US-PGPOD; 10.39	ľ
EFO, 0107	
DERWENT USPAT; 2003/11/0	4
212 (advanced ad) micro ad devices/.dom	i l
and (gate same width same mask) US-PGPUB; 10:48	
DERWENT	
1 (advanced adj micro adj devices).asn. USPAT; 2003/11/0	4
and (gate same width same mask same usage 10.49	
implementation) EPO; JPO; DERWENT	
) 4
27 (advanced adj micro adj devices).ash. US-PGPUB; 10:49	
EPO; SPO,	
DERWENT 2003/11//	14
[(advanced adj micro adj devices).asn. USPAT; 2003/11/0	73
and (gate same width same mask same US-regrot, 10.4)	
implantation)	
1 /6: ald add offect USPAT: 2003/11/	17
(angl\$3 with dopant)	
DERWENT	13
n i (innianting agi 1005) same (chicongi agi	
(conductive adj layer) of (gate adj	
electrode)) DERWENT	

	0	(inplanting adj ions) same (through adj	USPAT;	2004/05/13
		(conductive adj layer))	US-PGPUB; EPO; JPO;	12:14
			DERWENT	
-	0	\ <u></u>	USPAT;	2004/05/13
		adj layer)	US-PGPUB; EPO; JPO;	12:14
			DERWENT	
-	1379	(implanting adj ions) same (through adj	USPAT;	2004/05/13
		(conductive adj layer) or (gate adj	US-PGPUB;	12:16
İ		electrode))	EPO; JPO; DERWENT	
_	1243	(implanting adj ions) same (through adj	USPAT;	2004/05/13
		(conductive adj layer) or (gate adj	US-PGPUB;	12:16
1		electrode)) and semiconductor	EPO; JPO; DERWENT	
_	737	(implanting adj ions) same (through adj	USPAT;	2004/05/13
		(conductive adj layer) or (gate adj	US-PGPUB;	12:17
		electrode)) and semiconductor and etching	EPO; JPO;	
	551	and mask (implanting adj ions) same (through adj	DERWENT USPAT;	2004/05/13
_	331	(conductive adj layer) or (gate adj	US-PGPUB;	12:19
		electrode)) and semiconductor and etching	EPO; JPO;	
	100	and mask and @ad<20010716	DERWENT	2004/05/13
-	192	(implanting adj ions) near5 (through adj (conductive adj layer) or (gate adj	USPAT; US-PGPUB;	12:19
		electrode)) and semiconductor and etching	EPO; JPO;	
		and mask and @ad<20010716	DERWENT	0004/05/12
-	121	(implanting adj ions) near3 (through adj (conductive adj layer) or (gate adj	USPAT; US-PGPUB;	2004/05/13
		(conductive adj layer) of (gate adj electrode)) and semiconductor and etching	EPO; JPO;	12.15
		and mask and @ad<20010716	DERWENT	
-	88	(implanting adj ions) near2 (through adj	USPAT;	2004/05/13
		(conductive adj layer) or (gate adj electrode)) and semiconductor and etching	US-PGPUB; EPO; JPO;	12:35
	1	and mask and @ad<20010716	DERWENT	
-	88	(implanting adj ions) near2 (into adj	USPAT;	2004/05/13
		<pre>(conductive adj layer) or (gate adj electrode)) and semiconductor and etching</pre>	US-PGPUB; EPO; JPO;	12:56
		and mask and @ad<20010716	DERWENT	
_	88	(implanting adj ions) near2 (through adj	USPAT;	2004/05/21
	İ	(conductive adj layer) or (gate adj electrode)) and semiconductor and etching	US-PGPUB; EPO; JPO;	15:15
		and mask and @ad<20010716	DERWENT	
_	0	implanting adj ions adj through adj	USPAT;	2004/05/13
		conductive adj layer	US-PGPUB; EPO; JPO;	14:51
			DERWENT	
_	1	implanting adj through adj conductive adj	USPAT;	2004/05/21
		layer	US-PGPUB;	15:10
1			EPO; JPO; DERWENT	
-	5	implant\$3 adj through adj conductive adj	USPAT;	2004/05/21
		layer	US-PGPUB;	15:11
			EPO; JPO; DERWENT	
-	11	438/525.ccls. and (field adj effect adj	USPAT;	2004/05/13
		transistor) and (ion adj implant) and	US-PGPUB;	17:38
		(angl\$3 with dopant)	EPO; JPO; DERWENT	
_	0	438/525,197.ccls. and implant\$3 adj	USPAT;	2004/05/13
		through adj conductive adj layer	US-PGPUB;	17:37
			EPO; JPO; DERWENT	
_	16	438/197,525.ccls. and (field adj effect	USPAT;	2004/05/13
		adj transistor) and (ion adj implant) and	US-PGPUB;	17:38
		(angl\$3 with dopant)	EPO; JPO; DERWENT	
_	0	438/197,525.ccls. and (implant\$3 adj	USPAT;	2004/05/13
		through adj conductive adj layer)	US-PGPUB;	17:40
			EPO; JPO;	
	<u> </u>		DERWENT	<u></u>

4 1 5				
-	0	5822029.pn. and (black adj substrate)	USPAT;	2004/05/14
			US-PGPUB;	09:21
			EPO; JPO;	
			DERWENT	
-	1	implanting adj through adj conductive adj	USPAT;	2004/05/21
1		layer	US-PGPUB;	15:10
ŀ			EPO; JPO;	
			DERWENT	
_	0	implant\$3 adj through adj conductive adj	USPAT;	2004/05/21
		layer and (oblique adj angle)	US-PGPUB;	15:13
			EPO; JPO;	
	İ		DERWENT	
-	0	implant\$3 adj through adj conductive adj	USPAT;	2004/05/21
		layer and (oblique same implant\$3)	US-PGPUB;	15:14
			EPO; JPO;	
			DERWENT	
 	1217	oblique same implant\$3	USPAT;	2004/05/21
			US-PGPUB;	15:14
			EPO; JPO;	
			DERWENT	
-	3	(implanting adj ions) near2 (through adj	USPAT;	2004/05/21
		(conductive adj layer) or (gate adj	US-PGPUB;	15:15
		electrode)) and semiconductor and etching	EPO; JPO;	
		and mask and @ad<20010716 and (oblique	DERWENT	
		adj angle)		

L	Hits	Search Text	DB	Time stamp
Number				-
1	1309	438/197,230,231,289,290,298,301,302,303,30 and (field adj effect adj transistor) and (ion adj implant\$5) and @ad<20010716	US-PGPUB; EPO; JPO;	2004/05/25 16:58
2	76	438/197,230,231,289,290,298,301,302,303,30 and (field adj effect adj transistor) and (ion adj implant\$5) and @ad<20010716 and	DERWENT 5UGPAS; US-PGPUB; EPO; JPO;	2004/05/25 16:59
3	5	(angl\$3 with dopant)	DERWENT 5U8PAT; US-PGPUB; EPO; JPO;	2004/05/25 17:03
4	4	(angl\$3 with dopant) and (conductor same	DERWENT	2004/05/25 17:16
5	78	(angl\$3 with dopant) and (conductor same (ion adj implant\$5)) and mask 438/197,230,231,289,290,298,301,302,303,30 and (field adj effect adj transistor) and (ion adj implant\$5) and @ad<20010716 and	DERWENT	2004/05/25 17:17
6	0	(conductor same (ion adj implant\$5)) and	DERWENT	2004/05/25 17:18
7	11	(conductor same (ion adj implant\$5)) and mask and (pocket adj regions) 438/197,230,231,289,290,298,301,302,303,30 and (field adj effect adj transistor) and (ion adj implant\$5) and @ad<20010716 and	DERWENT 5U6 2AS; US-PGPUB; EPO; JPO;	2004/05/25 17:18
		(conductor same (ion adj implant\$5)) and mask and ((pocket or LDD) adj regions)	DERWENT	